Elektronische Bauelemente

2SC2229

50mA , 200V

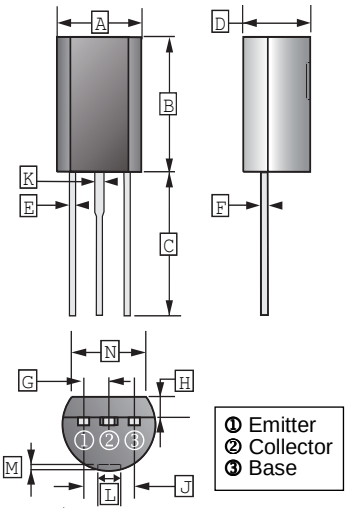
NPN Plastic Encapsulated Transistor

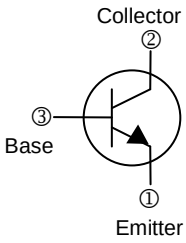
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Breakdown Voltage
- High Transition Frequency

TO-92MOD





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.50	6.50	H	1.70	2.05
B	8.00	9.00	J	2.70	3.20
C	12.70	14.50	K	0.85	1.15
D	4.50	5.30	L	1.60 Max	
E	0.35	0.65	M	0.00	0.40
F	0.30	0.51	N	4.00 Min	
G	1.50 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	800	mW
Thermal Resistance, Junction To Ambient	$R_{\theta JA}$	156	℃/W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	200	-	-	V	I_C=100μA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	150	-	-	V	I_C=1mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=100μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	0.1	μA	V_{CB}=200V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	0.1	μA	V_{EB}=5V, I_C=0
DC Current Gain	h_{FE}	70	-	240		V_{CE}=5V, I_C=10mA
		50	-	-		V_{CE}=5V, I_C=1mA
		50	-	-		V_{CE}=5V, I_C=50mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.5	V	I_C=10mA, I_B=1mA
Base to Emitter Saturation Voltage	V_{BE}	-	-	1	V	I_C=10mA, I_B=1mA
Transition Frequency	f_T	80	-	-	MHz	V_{CE}=30V, I_C=10mA

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CHARACTERISTIC CURVES